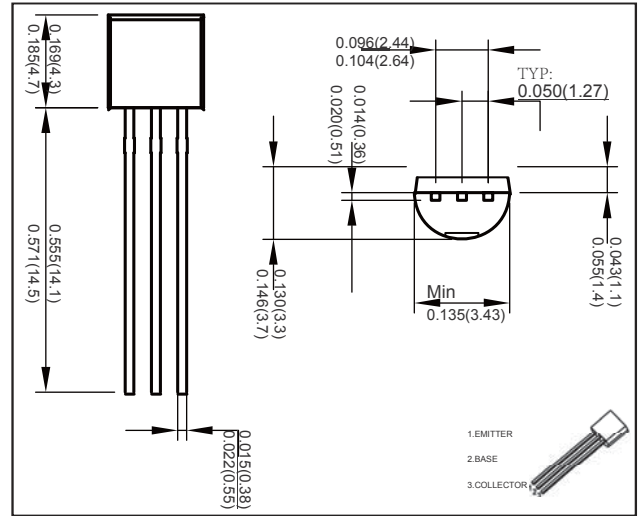


**TO-92 Plastic-Encapsulate Transistors**
**FEATURES**

- Switching and amplification in high voltage
- Applications such as telephony
- Low current(max. 600mA)
- High voltage(max.150V)
- PNP General Purpose Amplifier

**MECHANICAL DATA**

- Case style:TO-92 molded plastic
- Mounting position:any


**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-160	V
Collector-Emitter Voltage	$V_{CEO}$	-150	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-0.6	A
Collector Power Dissipation	$P_C$	625	mW
Thermal Resistance From Junction To Ambient	$R_{KJA}$	200	°C / W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~+150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.01mA, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -120V, I_E = 0$			-50	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -3V, I_C = 0$			-50	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5V, I_C = -1mA$	80			
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -1.0mA$	100		300	
	$h_{FE(3)}$	$V_{CE} = -5V, I_C = -5.0mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50mA, I_B = -5mA$			-1	V
Transition frequency	$f_T$	$V_{CE} = -5V, I_C = -10mA, f = 30MHz$	100		300	

 \* Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2.0\%$ .

## RATINGS AND CHARACTERISTIC CURVES

